

Silicon NPN Power Transistors

2SC4350

DESCRIPTION

- With TO-220 package
- High DC current gain
- DARLINGTON

APPLICATIONS

- For high speed power switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

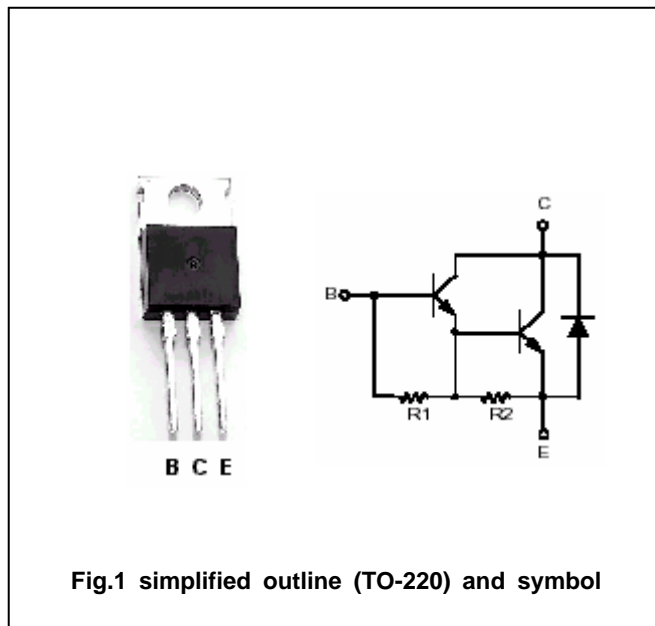


Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	100	V
V_{CEO}	Collector-emitter voltage	Open base	100	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		10	A
I_B	Base current		0.5	A
P_C	Collector power dissipation	$T_C=25$	40	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.1A ; I _B =0	100			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA; I _E =0;	100			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =5mA; I _C =0;	7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =5A; I _B =5mA			1.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =5A; I _B =5mA			2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =100V ; I _E =0			1	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =7V; I _C =0			5.0	mA
h _{FE}	DC current gain	I _C =5A ; V _{CE} =2V	2000		20000	

◆ h_{FE} classifications

M	L	K
2000-5000	4000-10000	8000-20000

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PACKAGE OUTLINE



Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)